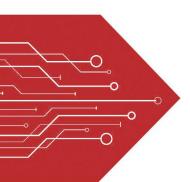
## MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

**PLED** 

# Broduct data sheet





SOD-123FL

## **FEATURES**

- \* Ideal for surface mount applications
- \* Easy pick and place
- \* Built-in strain relief
- \* Fast switching speed

## **MECHANICAL DATA**

- \* Case: Molded plastic
- \* Epoxy: UL 94V-0 rate flame retardant
- \* Metallurgically bonded construction
- \* Polarity: Color band denotes cathode end
- \* Mounting position: Any

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25°C ambient temperature unless otherwies specified. Single phase half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

TYPE NUMBER	U1A	U1B	U1D	U1G	U1J	U1K	U1M	UNITS
Maximum Recurrent Peak Reverse Voltage		100	200	400	600	800	1000	V
Maximum RMS Voltage		70	140	280	420	560	700	V
Maximum DC Blocking Voltage		100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current							•	
.375"(9.5mm) Lead Length at Ta=55°C		1.0			Α			
Peak Forward Surge Current, 8.3 ms single half sine-wave								
superimposed on rated load (JEDEC method)		30			Α			
Maximum Instantaneous Forward Voltage at 1.0A		1.0		1.3	1.7			V
Maximum DC Reverse Current Ta=25 C		5.0			μΑ			
at Rated DC Blocking Voltage Ta=100°C		100			μА			
Maximum Reverse Recovery Time (Note 1)		50		75			nS	
Typical Junction Capacitance (Note 2)	15			pF				
Operating and Storage Temperature Range Тл, Тsтс	-50 — +150			°C				

#### NOTES:

- 1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
- 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.



FIG.1-TYPICAL FORWARD

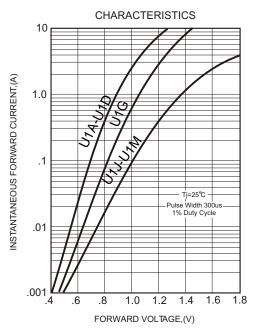
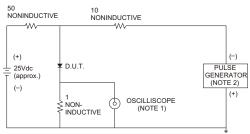


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE

#### RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.

2. Rise Time= 10ns max., Source Impedance= 50 ohms.

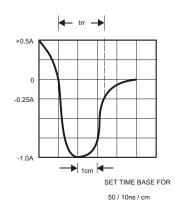


FIG.2-TYPICAL FORWARD CURRENT **DERATING CURVE** 

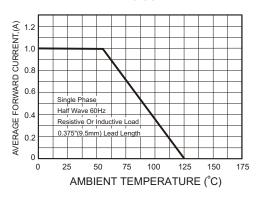


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

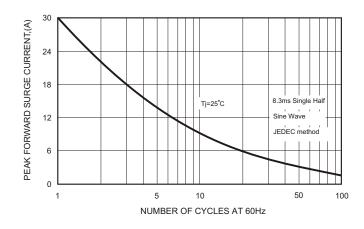
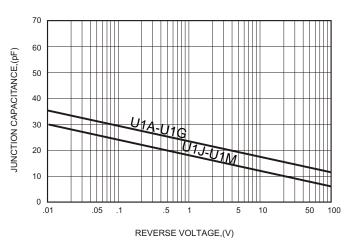
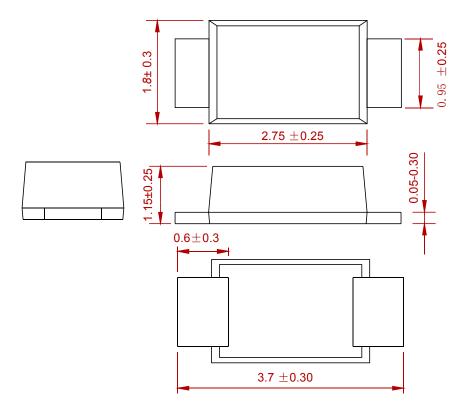


FIG.5-TYPICAL JUNCTION CAPACITANCE

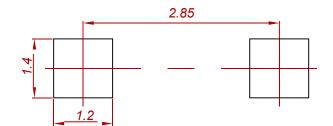


### **PACKAGE MECHANICAL DATA**



Dimensions in millimeters

## **Suggested Pad Layout**



#### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

## **REEL SPECIFICATION**

P/N	PKG	QTY
U1A THRU U1M	SOD-123FL	3000



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